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cut Particularly, such phenomenon tends to occur at the time of switching on/off the plasma.

Beginning at page 4, line 8,

A2 Summary of the Invention

Beginning at page 7, line 2,

A3 (6) Even when the temperature of the base is lowered, the large kinetic energy of the reactive species enables formation of a film of good quality. therefore, the temperature of the base can be further lowered and a large and inexpensive insulating substrate such as a glass substrate or a heat-resistant resin substrate can be used to reduce the cost.

Beginning at page 10, line 1,

A4 Detailed Description of the Preferred Embodiments

Beginning at page 25, line 18,

A5 The substrate 1 is heated from the room temperature to 550°C, for example, 200 to 300°C, by the heater wire 51 in the susceptor 45, and the catalyzer 46 is heated for activation to a temperature not higher than the melting point, particularly 800 to 2000°C, as a resistance wire in the hydrogen-based carrier gas, for example, by heating a tungsten wire to approximately 1650°C for activation. The reaction gas 40 is brought in contact with the heated catalyzer 46 of tungsten or the like, and the shutter 47 is opened.
